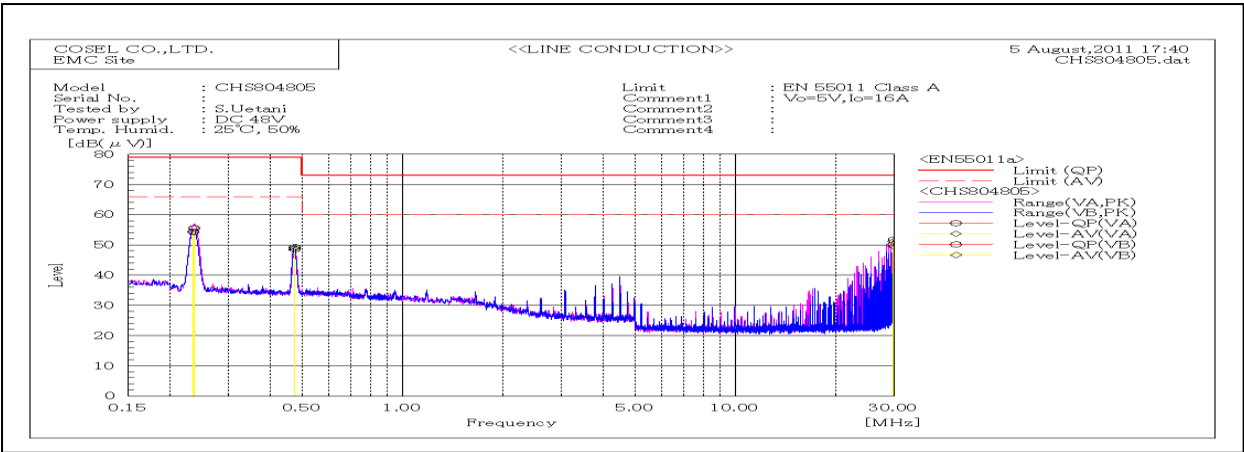
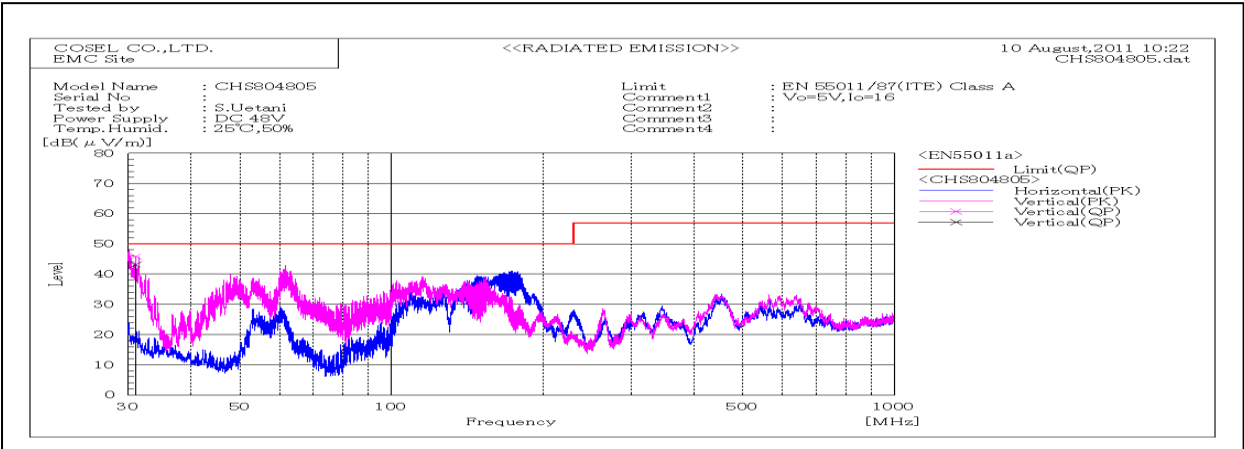


DATA SHEET		Date	27-Apr-21
Model	CHS804805	Temp.	25 degreeC
Test	EMI Line conduction & Radiated emission	Humid.	40 %RH
		Tested by	S.Uetani



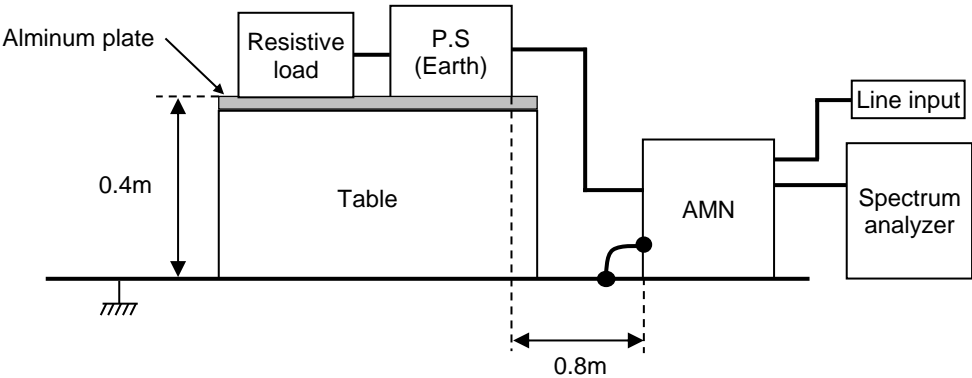
Frequency MHz	Harm	Line Phase	Reading dB(μV)		Factor dB	Level dB(μV)		Limit dB(μV)		Margin dB		Pass/ Fail	Remark
			QP	AV		QP	AV	QP	AV	QP	AV		
0.23543		VB	44.2	44.2	10.1	54.3	54.3	79	66	24.7	11.7	Pass	
0.23657		VA	45.5	45.6	10.1	55.6	55.7	79	66	23.4	10.3	Pass	
0.47482		VA	38.5	38.2	10.1	48.6	48.3	79	66	30.4	17.7	Pass	
0.47405		VB	39.2	38.9	10.1	49.3	49	79	66	29.7	17	Pass	
29.8124		VB	39.2	38.6	11	50.2	49.6	73	60	22.8	10.4	Pass	
29.80625		VA	40.7	40	11	51.7	51	73	60	21.3	9	Pass	



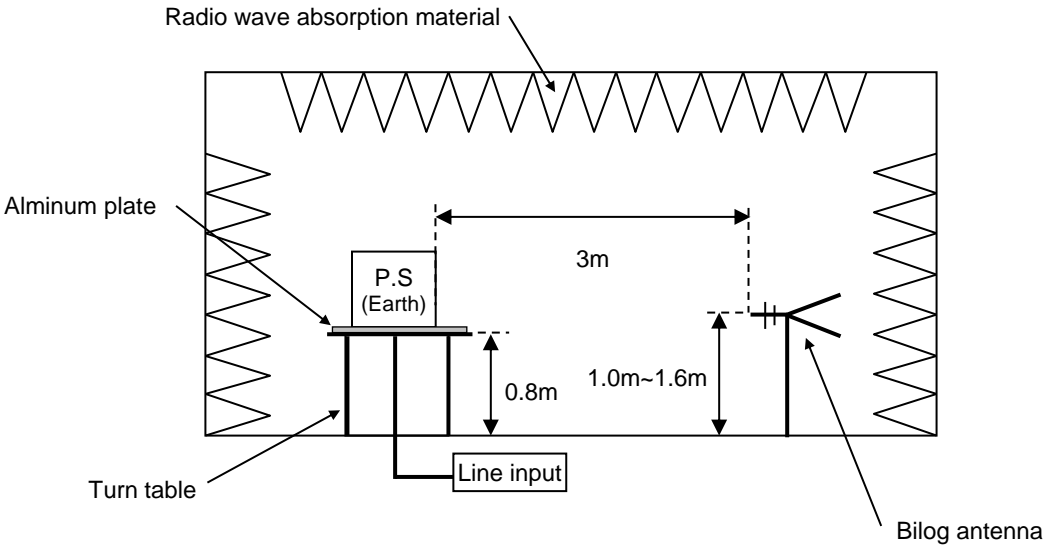
Frequency MHz	Harm	Polariz ation	Stabili ty	Reading dB(μV)		Space Loss dB	Level dB(mW)		Margin dB	Pass/ Fail	Height cm	Angle deg	Remark
				QP	AV		QP	AV					
31.038		V	Stable	57		-13.9	43.1		50	6.9	Pass	102	131

DATA SHEET		Date	27-Apr-21
Model	Circuit used for measurement	Temp.	25 degreeC
Test	EMI Line conduction & Radiated emission	Humid.	40 %RH
		Tested by	S.Uetani

1. Line conduction



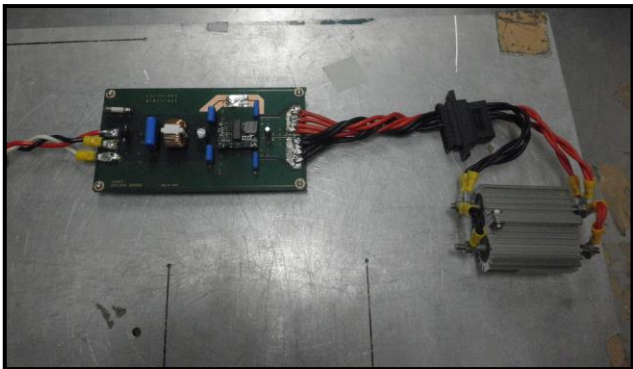
2. Radiated emission



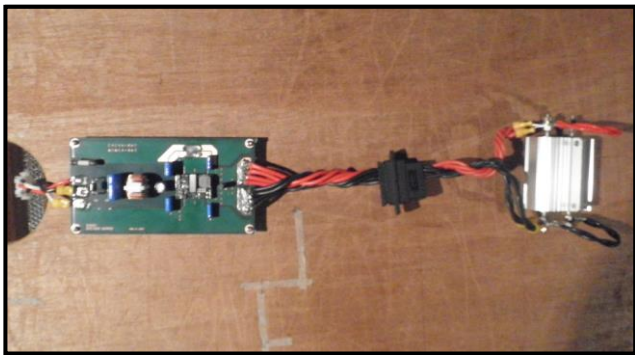
TEST :EMI
Model Name :CHS804805

Date 2011/10/4

○Photographs of Test Set-Up
LINE CONDUCTION



RADIATED EMISSION



○ Testing circuitry

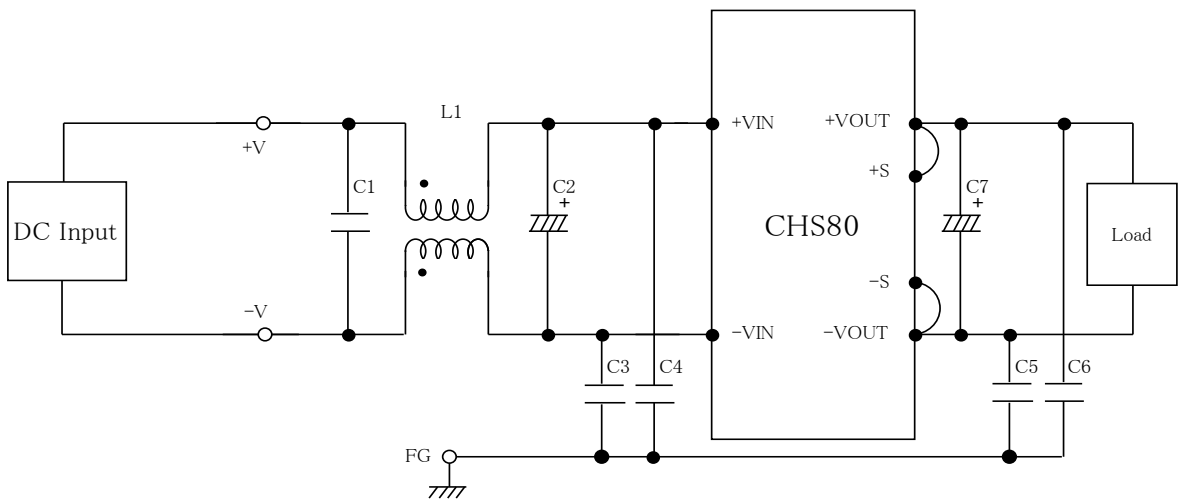


Fig.1 Testing circuitry

- L1 : 1mH SC-05-10J (TOKIN)
- C1 : 250V 2.2 μ F FPD22E225J4 (NITSUKO)
- C2 : 100V 33 μ F PWseries (nichicon)
- C3,C4 : 630V 0.068 μ F FPD22J683J4(NITSUKO)
- C5,C6 : 630V 0.033 μ F FPD22J333J4(NITSUKO)
- C7 : 50V 10 μ F PMseries (nichicon)